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Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	PowerPC e300c2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA
Supplier Device Package	516-PBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8323evraddca

1.3 Security Engine

The security engine is optimized to handle all the algorithms associated with IPSec, IEEE 802.11i™ standard, and iSCSI. The security engine contains one crypto-channel, a controller, and a set of crypto execution units (EUs). The execution units are:

- Data encryption standard execution unit (DEU), supporting DES and 3DES
- Advanced encryption standard unit (AESU), supporting AES
- Message digest execution unit (MDEU), supporting MD5, SHA1, SHA-256, and HMAC with any algorithm
- One crypto-channel supporting multi-command descriptor chains

1.4 DDR Memory Controller

The MPC8323E DDR1/DDR2 memory controller includes the following features:

- Single 32-bit interface supporting both DDR1 and DDR2 SDRAM
- Support for up to 266-MHz data rate
- Support for two $\times 16$ devices
- Support for up to 16 simultaneous open pages
- Supports auto refresh
- On-the-fly power management using CKE
- 1.8-/2.5-V SSTL2 compatible I/O
- Support for 1 chip select only
- FCRAM, ECC, hardware/software calibration, bit deskew, QIN stage, or atomic logic are not supported.

1.5 PCI Controller

The MPC8323E PCI controller includes the following features:

- *PCI Specification Revision 2.3* compatible
- Single 32-bit data PCI interface operates up to 66 MHz
- PCI 3.3-V compatible (not 5-V compatible)
- Support for host and agent modes
- On-chip arbitration, supporting three external masters on PCI
- Selectable hardware-enforced coherency

1.6 Programmable Interrupt Controller (PIC)

The programmable interrupt controller (PIC) implements the necessary functions to provide a flexible solution for general-purpose interrupt control. The PIC programming model is compatible with the MPC8260 interrupt controller, and it supports 8 external and 35 internal discrete interrupt sources. Interrupts can also be redirected to an external interrupt controller.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8323E. The MPC8323E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings¹

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage		AV_{DDn}	–0.3 to 1.26	V	—
DDR1 and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
PCI, local bus, DUART, system control and power management, I ² C, SPI, MII, RMII, MII management, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.6	V	—
Input voltage	DDR1/DDR2 DRAM signals	MV_{IN}	–0.3 to ($GV_{DD} + 0.3$)	V	2
	DDR1/DDR2 DRAM reference	MV_{REF}	–0.3 to ($GV_{DD} + 0.3$)	V	2
	Local bus, DUART, CLKIN, system control and power management, I ² C, SPI, and JTAG signals	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	3
	PCI	OV_{IN}	–0.3 to ($OV_{DD} + 0.3$)	V	5
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:

- Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
- Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.

Table 11. Reset Signals DC Electrical Characteristics (continued)

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input current	I_{IN}	$0\text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA	—

Note:

1. This specification applies when operating from 3.3 V supply.

6 DDR1 and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR1 and DDR2 SDRAM interface of the MPC8323E. Note that DDR1 SDRAM is $Dn_GV_{DD}(\text{typ}) = 2.5\text{ V}$ and DDR2 SDRAM is $Dn_GV_{DD}(\text{typ}) = 1.8\text{ V}$. The AC electrical specifications are the same for DDR1 and DDR2 SDRAM.

6.1 DDR1 and DDR2 SDRAM DC Electrical Characteristics

Table 12 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8323E when $Dn_GV_{DD}(\text{typ}) = 1.8\text{ V}$.

Table 12. DDR2 SDRAM DC Electrical Characteristics for $Dn_GV_{DD}(\text{typ}) = 1.8\text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	Dn_GV_{DD}	1.71	1.89	V	1
I/O reference voltage	$MVREFn_{REF}$	$0.49 \times Dn_GV_{DD}$	$0.51 \times Dn_GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MVREFn_{REF} - 0.04$	$MVREFn_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MVREFn_{REF} + 0.125$	$Dn_GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	−0.3	$MVREFn_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	−9.9	9.9	μA	4
Output high current ($V_{OUT} = 1.35\text{ V}$)	I_{OH}	−13.4	—	mA	—
Output low current ($V_{OUT} = 0.280\text{ V}$)	I_{OL}	13.4	—	mA	—

Notes:

- Dn_GV_{DD} is expected to be within 50 mV of the DRAM Dn_GV_{DD} at all times.
- $MVREFn_{REF}$ is expected to be equal to $0.5 \times Dn_GV_{DD}$, and to track Dn_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MVREFn_{REF}$ may not exceed $\pm 2\%$ of the DC value.
- V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to $MVREFn_{REF}$. This rail should track variations in the DC level of $MVREFn_{REF}$.
- Output leakage is measured with all outputs disabled, $0\text{ V} \leq V_{OUT} \leq Dn_GV_{DD}$.

Table 13 provides the DDR2 capacitance when $Dn_GV_{DD}(\text{typ}) = 1.8\text{ V}$.

Table 13. DDR2 SDRAM Capacitance for $Dn_GV_{DD}(\text{typ}) = 1.8\text{ V}$

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1

6.2 DDR1 and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR1 and DDR2 SDRAM interface.

6.2.1 DDR1 and DDR2 SDRAM Input AC Timing Specifications

Table 16 provides the input AC timing specifications for the DDR2 SDRAM ($Dn_GV_{DD}(typ) = 1.8\text{ V}$).

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with Dn_GV_{DD} of $1.8 \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MVREFn_{REF} - 0.25$	V	—
AC input high voltage	V_{IH}	$MVREFn_{REF} + 0.25$	—	V	—

Table 17 provides the input AC timing specifications for the DDR1 SDRAM ($Dn_GV_{DD}(typ) = 2.5\text{ V}$).

Table 17. DDR1 SDRAM Input AC Timing Specifications for 2.5 V Interface

At recommended operating conditions with Dn_GV_{DD} of $2.5 \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MVREFn_{REF} - 0.31$	V	—
AC input high voltage	V_{IH}	$MVREFn_{REF} + 0.31$	—	V	—

Table 18 provides the input AC timing specifications for the DDR1 and DDR2 SDRAM interface.

Table 18. DDR1 and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with Dn_GV_{DD} of $(1.8\text{ or }2.5\text{ V}) \pm 5\%$.

Parameter	Symbol	Min	Max	Unit	Notes
Controller skew for MDQS—MDQ/MDM	t_{CISKEW}			ps	1, 2
266 MHz		–750	750		
200 MHz		–1250	1250		

Notes:

- t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This should be subtracted from the total timing budget.
- The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW} . This can be determined by the following equation: $t_{DISKEW} = \pm(T/4 - \text{abs}(t_{CISKEW}))$ where T is the clock period and $\text{abs}(t_{CISKEW})$ is the absolute value of t_{CISKEW} .

Figure 4 shows the input timing diagram for the DDR controller.

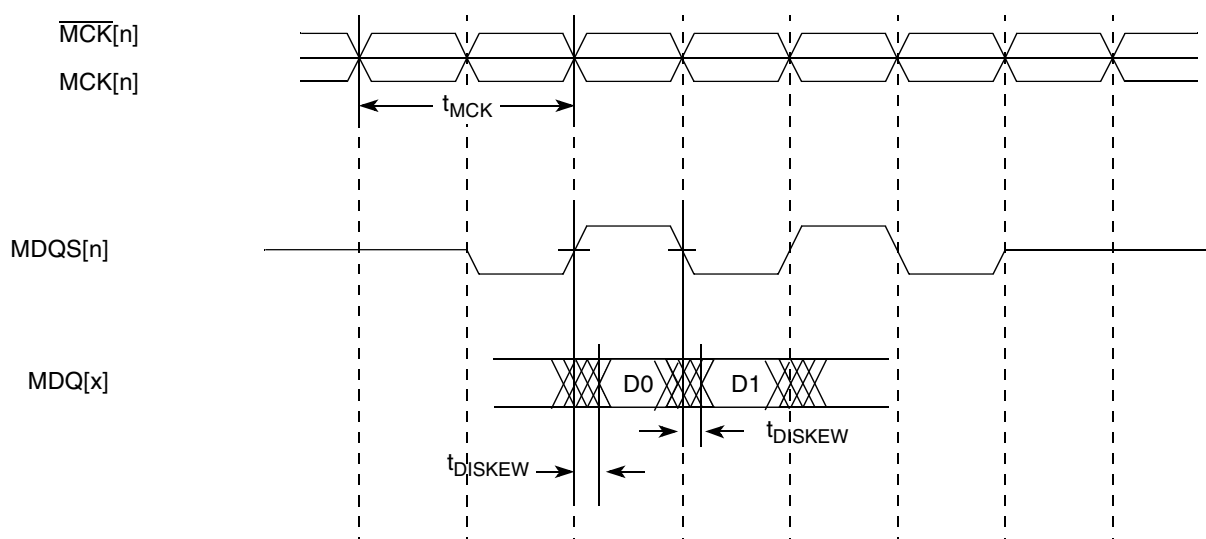


Figure 4. DDR Input Timing Diagram

6.2.2 DDR1 and DDR2 SDRAM Output AC Timing Specifications

Table 19 provides the output AC timing specifications for the DDR1 and DDR2 SDRAM interfaces.

Table 19. DDR1 and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with Dn_GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK cycle time, (MCK/ $\overline{\text{MCK}}$ crossing)	t_{MCK}	7.5	10	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHAS}	2.5 3.5	— —	ns	3
ADDR/CMD output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHAX}	2.5 3.5	— —	ns	3
$\overline{\text{MCS}}$ output setup with respect to MCK 266 MHz 200 MHz	t_{DDKHCS}	2.5 3.5	— —	ns	3
$\overline{\text{MCS}}$ output hold with respect to MCK 266 MHz 200 MHz	t_{DDKHCX}	2.5 3.5	— —	ns	3
MCK to MDQS Skew	t_{DDKMHM}	-0.6	0.6	ns	4

8.2.2.1 RMII Transmit AC Timing Specifications

Table 23 provides the RMII transmit AC timing specifications.

Table 25. RMII Transmit AC Timing Specifications

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$	2	—	10	ns
REF_CLK data clock rise $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	t_{RMXF}	1.0	—	4.0	ns

Note:

- The symbols used for timing specifications follow the pattern of $t_{(\text{first three letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 10 shows the RMII transmit AC timing diagram.

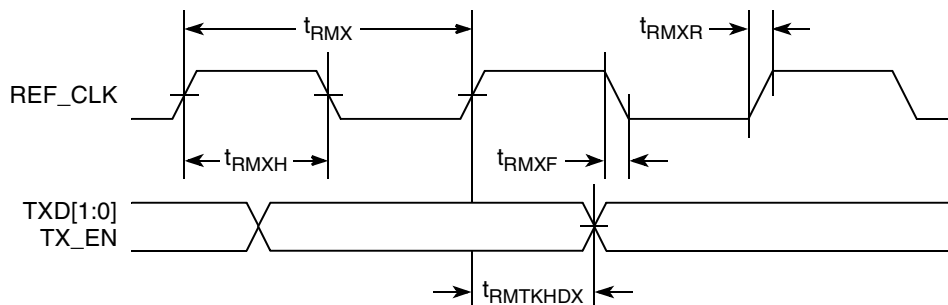


Figure 10. RMII Transmit AC Timing Diagram

8.2.2.2 RMII Receive AC Timing Specifications

Table 24 provides the RMII receive AC timing specifications.

Table 26. RMII Receive AC Timing Specifications

At recommended operating conditions with OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typical	Max	Unit
REF_CLK clock period	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	$t_{RMRDVKH}$	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	$t_{RMRDXKH}$	2.0	—	—	ns
REF_CLK clock rise $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	t_{RMXR}	1.0	—	4.0	ns

Table 32. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock to output high impedance:				ns	
Boundary-scan data	t_{JTKLDZ}	2	19		5, 6
TDO	t_{JTKLOZ}	2	9		6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50- Ω load (see Figure 14). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDVXH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. \overline{TRST} is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design and characterization.

Figure 18 provides the AC test load for TDO and the boundary-scan outputs of the MPC8323E.

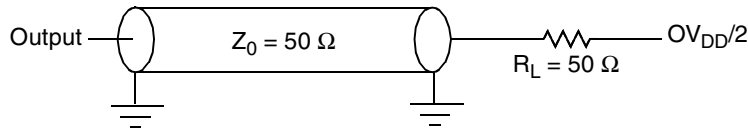

Figure 18. AC Test Load for the JTAG Interface

Figure 19 provides the JTAG clock input timing diagram.

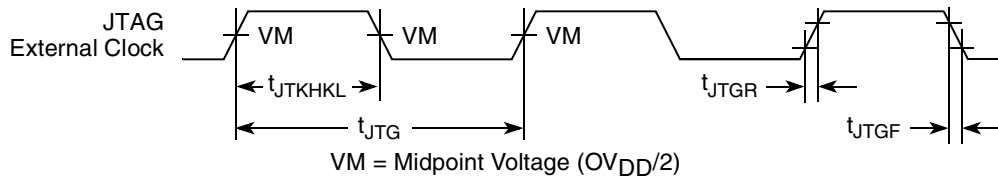

Figure 19. JTAG Clock Input Timing Diagram

Figure 20 provides the \overline{TRST} timing diagram.

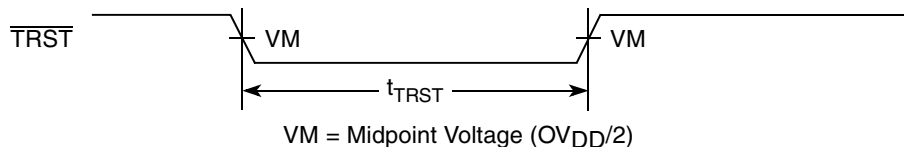

Figure 20. \overline{TRST} Timing Diagram

Figure 31 and Figure 32 represent the AC timing from Table 45. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 31 shows the SPI timing in slave mode (external clock).

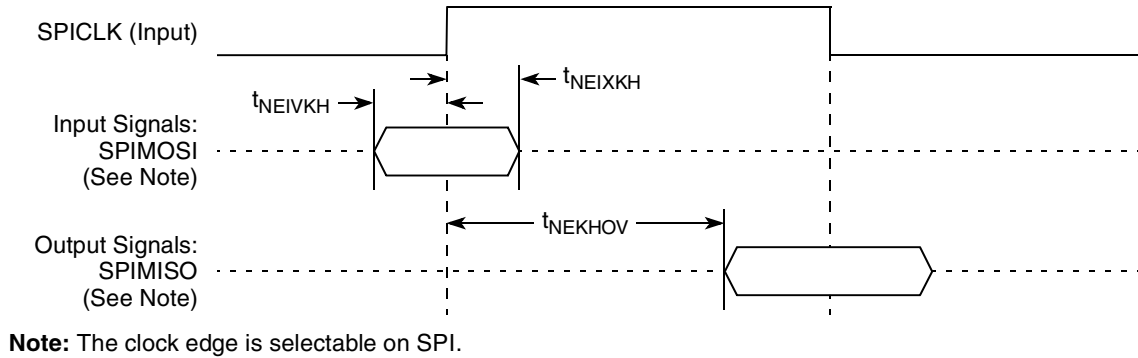


Figure 31. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 32 shows the SPI timing in master mode (internal clock).

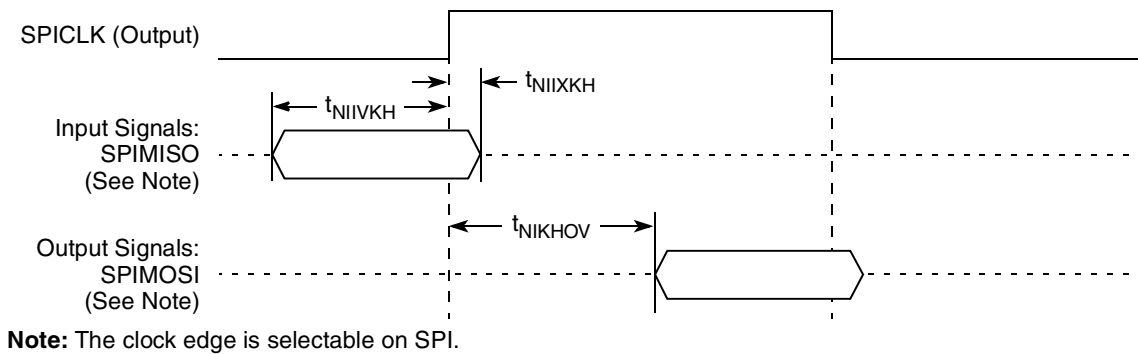


Figure 32. SPI AC Timing in Master Mode (Internal Clock) Diagram

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8323E.

17.1 TDM/SI DC Electrical Characteristics

Table 46 provides the DC electrical characteristics for the MPC8323E TDM/SI.

Table 46. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V

19 HDLC, BISYNC, Transparent, and Synchronous UART

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), BISYNC, transparent, and synchronous UART of the MPC8323E.

19.1 HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the MPC8323E HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 50. HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V
Output low voltage	V_{OL}	$I_{OL} = 3.2 \text{ mA}$	—	0.5	V
Input high voltage	V_{IH}	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	-0.3	0.8	V
Input current	I_{IN}	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	± 5	μA

19.2 HDLC, BISYNC, Transparent, and Synchronous UART AC Timing Specifications

Table 51 provides the input and output AC timing specifications for HDLC, BISYNC, and transparent UART protocols.

Table 51. HDLC, BISYNC, and Transparent UART AC Timing Specifications¹

Characteristic	Symbol ²	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	5.5	ns
Outputs—External clock delay	t_{HEKHOV}	1	10	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	0	5.5	ns
Outputs—External clock high impedance	t_{HEKHOX}	1	8	ns
Inputs—Internal clock input setup time	t_{HIIVKH}	6	—	ns
Inputs—External clock input setup time	t_{HEIVKH}	4	—	ns
Inputs—Internal clock input hold time	t_{HIIXKH}	0	—	ns

20 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8323E.

20.1 USB DC Electrical Characteristics

Table 53 provides the DC electrical characteristics for the USB interface.

Table 53. USB DC Electrical Characteristics¹

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	-0.3	0.8	V
High-level output voltage, $I_{OH} = -100 \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100 \mu A$	V_{OL}	—	0.2	V
Input current	I_{IN}	—	± 5	μA

Note:

- Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

20.2 USB AC Electrical Specifications

Table 54 describes the general timing parameters of the USB interface of the MPC8323E.

Table 54. USB General Timing Parameters

Parameter	Symbol ¹	Min	Max	Unit	Notes
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions

Notes:

- The symbols used for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(state)(signal)}$ for receive signals and $t_{(first\ two\ letters\ of\ functional\ block)(state)(signal)}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
- Skew measurements are done at $OV_{DD}/2$ of the rising or falling edge of the signals.

Figure 41 provide the AC test load for the USB.

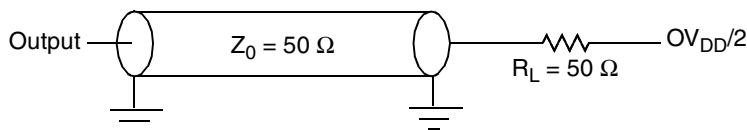


Figure 41. USB AC Test Load

21 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8323E is available in a thermally enhanced Plastic Ball Grid Array (PBGA); see [Section 21.1, “Package Parameters for the MPC8323E PBGA,”](#) and [Section 21.2, “Mechanical Dimensions of the MPC8323E PBGA,”](#) for information on the PBGA.

21.1 Package Parameters for the MPC8323E PBGA

The package parameters are as provided in the following list. The package type is 27 mm × 27 mm, 516 PBGA.

Package outline	27 mm × 27 mm
Interconnects	516
Pitch	1.00 mm
Module height (typical)	2.25 mm
Solder Balls	62 Sn/36 Pb/2 Ag (ZQ package) 95.5 Sn/0.5 Cu/4Ag (VR package)
Ball diameter (typical)	0.6 mm

21.2 Mechanical Dimensions of the MPC8323E PBGA

[Figure 42](#) shows the mechanical dimensions and bottom surface nomenclature of the MPC8323E, 516-PBGA package.

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Power and Ground Supplies				
AV _{DD} 1	P3	I	AV _{DD} 1	—
AV _{DD} 2	AA1	I	AV _{DD} 2	—
AV _{DD} 3	AB15	I	AV _{DD} 3	—
AV _{DD} 4	C24	I	AV _{DD} 4	—
MVREF1	AB8	I	DDR reference voltage	—
MVREF2	AB17	I	DDR reference voltage	—
PCI				
PCI_INTA /IRQ_OUT	AF2	O	OV _{DD}	2
PCI_RESET_OUT	AE2	O	OV _{DD}	—
PCI_AD0/MSRCID0 (DDR ID)	L1	IO	OV _{DD}	—
PCI_AD1/MSRCID1 (DDR ID)	L2	IO	OV _{DD}	—
PCI_AD2/MSRCID2 (DDR ID)	M1	IO	OV _{DD}	—
PCI_AD3/MSRCID3 (DDR ID)	M2	IO	OV _{DD}	—
PCI_AD4/MSRCID4 (DDR ID)	L3	IO	OV _{DD}	—
PCI_AD5/MDVAL (DDR ID)	N1	IO	OV _{DD}	—
PCI_AD6	N2	IO	OV _{DD}	—
PCI_AD7	M3	IO	OV _{DD}	—
PCI_AD8	P1	IO	OV _{DD}	—
PCI_AD9	R1	IO	OV _{DD}	—
PCI_AD10	N3	IO	OV _{DD}	—
PCI_AD11	N4	IO	OV _{DD}	—
PCI_AD12	T1	IO	OV _{DD}	—
PCI_AD13	R2	IO	OV _{DD}	—
PCI_AD14/ECID_TMODE_IN	T2	IO	OV _{DD}	—
PCI_AD15	U1	IO	OV _{DD}	—
PCI_AD16	Y2	IO	OV _{DD}	—
PCI_AD17	Y1	IO	OV _{DD}	—
PCI_AD18	AA2	IO	OV _{DD}	—
PCI_AD19	AB1	IO	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_AD20	AB2	IO	OV _{DD}	—
PCI_AD21	Y4	IO	OV _{DD}	—
PCI_AD22	AC1	IO	OV _{DD}	—
PCI_AD23	AA3	IO	OV _{DD}	—
PCI_AD24	AA4	IO	OV _{DD}	—
PCI_AD25	AD1	IO	OV _{DD}	—
PCI_AD26	AD2	IO	OV _{DD}	—
PCI_AD27	AB3	IO	OV _{DD}	—
PCI_AD28	AB4	IO	OV _{DD}	—
PCI_AD29	AE1	IO	OV _{DD}	—
PCI_AD30	AC3	IO	OV _{DD}	—
PCI_AD31	AC4	IO	OV _{DD}	—
PCI_C_BE0	M4	IO	OV _{DD}	—
PCI_C_BE1	T4	IO	OV _{DD}	—
PCI_C_BE2	Y3	IO	OV _{DD}	—
PCI_C_BE3	AC2	IO	OV _{DD}	—
PCI_PAR	U3	IO	OV _{DD}	—
PCI_FRAME	W1	IO	OV _{DD}	5
PCI_TRDY	W4	IO	OV _{DD}	5
PCI_IRDY	W2	IO	OV _{DD}	5
PCI_STOP	V4	IO	OV _{DD}	5
PCI_DEVSEL	W3	IO	OV _{DD}	5
PCI_IDSEL	P2	I	OV _{DD}	—
PCI_SERR	U4	IO	OV _{DD}	5
PCI_PERR	V3	IO	OV _{DD}	5
PCI_REQ0	AD4	IO	OV _{DD}	—
PCI_REQ1/CPCI_HS_ES	AE3	I	OV _{DD}	—
PCI_REQ2	AF3	I	OV _{DD}	—
PCI_GNT0	AD3	IO	OV _{DD}	—
PCI_GNT1/CPCI_HS_LED	AE4	O	OV _{DD}	—
PCI_GNT2/CPCI_HS_ENUM	AF4	O	OV _{DD}	—
M66EN	L4	I	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PA26/Enet2_RX_ER/SER2_CD/TDMB_REQ/LA10 (LBIU)	E26	IO	OV _{DD}	—
GPIO_PA27/Enet2_TX_ER/TDMB_CLKO/LA11 (LBIU)	F25	IO	OV _{DD}	—
GPIO_PA28/Enet2_RX_DV/SER2_CTS/TDMB_RSYNC/LA12 (LBIU)	E25	IO	OV _{DD}	—
GPIO_PA29/Enet2_COL/RXD[4]/SER2_RXD[4]/TDMB_STROBE/LA13 (LBIU)	J25	IO	OV _{DD}	—
GPIO_PA30/Enet2_TX_EN/SER2_RTS/TDMB_TSYNC/LA14 (LBIU)	F26	IO	OV _{DD}	—
GPIO_PA31/Enet2_CRS/SDET LA15 (LBIU)	J26	IO	OV _{DD}	—
GPIO_PB0/Enet3_TXD[0]/SER3_TXD[0]/TDMC_TXD[0]	A13	IO	OV _{DD}	—
GPIO_PB1/Enet3_TXD[1]/SER3_TXD[1]/TDMC_TXD[1]	B13	IO	OV _{DD}	—
GPIO_PB2/Enet3_TXD[2]/SER3_TXD[2]/TDMC_TXD[2]	A14	IO	OV _{DD}	—
GPIO_PB3/Enet3_TXD[3]/SER3_TXD[3]/TDMC_TXD[3]	B14	IO	OV _{DD}	—
GPIO_PB4/Enet3_RXD[0]/SER3_RXD[0]/TDMC_RXD[0]	B8	IO	OV _{DD}	—
GPIO_PB5/Enet3_RXD[1]/SER3_RXD[1]/TDMC_RXD[1]	A8	IO	OV _{DD}	—
GPIO_PB6/Enet3_RXD[2]/SER3_RXD[2]/TDMC_RXD[2]	A9	IO	OV _{DD}	—
GPIO_PB7/Enet3_RXD[3]/SER3_RXD[3]/TDMC_RXD[3]	B9	IO	OV _{DD}	—
GPIO_PB8/Enet3_RX_ER/SER3_CD/TDMC_REQ	A11	IO	OV _{DD}	—
GPIO_PB9/Enet3_TX_ER/TDMC_CLKO	B11	IO	OV _{DD}	—
GPIO_PB10/Enet3_RX_DV/SER3_CTS/TDMC_RSYNC	A10	IO	OV _{DD}	—
GPIO_PB11/Enet3_COL/RXD[4]/SER3_RXD[4]/TDMC_STROBE	A15	IO	OV _{DD}	—
GPIO_PB12/Enet3_TX_EN/SER3_RTS/TDMC_TSYNC	B12	IO	OV _{DD}	—
GPIO_PB13/Enet3_CRS/SDET	B15	IO	OV _{DD}	—
GPIO_PB14/CLK12	D9	IO	OV _{DD}	—
GPIO_PB15 UPC1_TxADDR[4]	D14	IO	OV _{DD}	—
GPIO_PB16 UPC1_RxADDR[4]	B16	IO	OV _{DD}	—

Table 55. MPC8323E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GPIO_PD10/GTM1_TIN2/GTM2_TIN1/CLK17	J24	IO	OV _{DD}	—
GPIO_PD11/GTM1_TGATE2/GTM2_TGATE1	B25	IO	OV _{DD}	—
GPIO_PD12/GTM1_TOUT2/GTM2_TOUT1	C4	IO	OV _{DD}	—
GPIO_PD13/GTM1_TIN3/GTM2_TIN4/BRGO8	D4	IO	OV _{DD}	—
GPIO_PD14/GTM1_TGATE3/GTM2_TGATE4	D5	IO	OV _{DD}	—
GPIO_PD15/GTM1_TOUT3	A5	IO	OV _{DD}	—
GPIO_PD16/GTM1_TIN4/GTM2_TIN3	B5	IO	OV _{DD}	—
GPIO_PD17/GTM1_TGATE4/GTM2_TGATE3	C5	IO	OV _{DD}	—
GPIO_PD18/GTM1_TOUT4/GTM2_TOUT3	A6	IO	OV _{DD}	—
GPIO_PD19/CE_RISC1_INT/CE_EXT_REQ4	B6	IO	OV _{DD}	—
GPIO_PD20/CLK18/BRGO6	D21	IO	OV _{DD}	—
GPIO_PD21/CLK16/BRGO5/UPC1_CLKO	C19	IO	OV _{DD}	—
GPIO_PD22/CLK4/BRGO9/UCC2_CLKO	A7	IO	OV _{DD}	—
GPIO_PD23/CLK3/BRGO10/UCC3_CLKO	B7	IO	OV _{DD}	—
GPIO_PD24/CLK10/BRGO2/UCC4_CLKO	A12	IO	OV _{DD}	—
GPIO_PD25/CLK13/BRGO16/UCC5_CLKO	B10	IO	OV _{DD}	—
GPIO_PD26/CLK2/BRGO4/UCC1_CLKO	E4	IO	OV _{DD}	—
GPIO_PD27/CLK1/BRGO3	F4	IO	OV _{DD}	—
GPIO_PD28/CLK19/BRGO11	D15	IO	OV _{DD}	—
GPIO_PD29/CLK15/BRGO8	C6	IO	OV _{DD}	—
GPIO_PD30/CLK14	D6	IO	OV _{DD}	—
GPIO_PD31/CLK7/BRGO15	E24	IO	OV _{DD}	—
Power and Ground Supplies				
GV _{DD}	AA8, AA10, AA11, AA13, AA14, AA16, AA17, AA19, AA21, AB9, AB10, AB11, AB12, AB14, AB18, AB20, AB21, AC6, AC8, AC14, AC18	GV _{DD}	—	—
OV _{DD}	E5, E6, E8, E9, E10, E12, E14, E15, E16, E18, E19, E20, E22, F5, F6, F8, F10, F14, F16, F19, F22, G22, H5, H6, H21, J5, J22, K21, K22, L5, L6, L22, M5, M22, N5, N21, N22, P6, P22, P23, R5, R23, T5, T21, T22, U6, U22, V5, V22, W22, Y5, AB5, AB6, AC5	OV _{DD}	—	—

22.5 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 60 shows the encodings for RCWL[COREPLL]. COREPLL values not listed in Table 60 should be considered reserved.

Table 60. e300 Core PLL Configuration

RCWL[COREPLL]			<i>core_clk</i> : <i>csb_clk</i> Ratio	VCO Divider
0-1	2-5	6		
nn	0000	n	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)
00	0001	0	1:1	÷2
01	0001	0	1:1	÷4
10	0001	0	1:1	÷8
11	0001	0	1:1	÷8
00	0001	1	1.5:1	÷2
01	0001	1	1.5:1	÷4
10	0001	1	1.5:1	÷8
11	0001	1	1.5:1	÷8
00	0010	0	2:1	÷2
01	0010	0	2:1	÷4
10	0010	0	2:1	÷8
11	0010	0	2:1	÷8
00	0010	1	2.5:1	÷2
01	0010	1	2.5:1	÷4
10	0010	1	2.5:1	÷8
11	0010	1	2.5:1	÷8
00	0011	0	3:1	÷2
01	0011	0	3:1	÷4
10	0011	0	3:1	÷8
11	0011	0	3:1	÷8

NOTE

Core VCO frequency = core frequency × VCO divider

VCO divider (RCWL[COREPLL[0:1]]) must be set properly so that the core VCO frequency is in the range of 500–800 MHz.

22.6 QUICC Engine PLL Configuration

The QUICC Engine PLL is controlled by the RCWL[CEPMF] and RCWL[CEPDF] parameters. [Table 61](#) shows the multiplication factor encodings for the QUICC Engine PLL.

Table 61. QUICC Engine PLL Multiplication Factors

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/(1 + RCWL[CEPDF])
00000–00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001–11111	0	Reserved

The RCWL[CEVCOD] denotes the QUICC Engine PLL VCO internal frequency as shown in [Table 62](#).

Table 62. QUICC Engine PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine VCO frequency is in the range of 300–600 MHz. The QUICC Engine frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine frequencies should be selected according to the performance requirements.

The QUICC Engine VCO frequency is derived from the following equations:

$$ce_clk = (\text{primary clock input} \times \text{CEPMF}) \div (1 + \text{CEPDF})$$

$$\text{QUICC Engine VCO Frequency} = ce_clk \times \text{VCO divider} \times (1 + \text{CEPDF})$$

interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8323E.

24.1 System Clocking

The MPC8323E includes three PLLs.

- The system PLL (AV_{DD2}) generates the system clock from the externally supplied CLKIN input. The frequency ratio between the system and CLKIN is selected using the system PLL ratio configuration bits as described in [Section 22.4, “System PLL Configuration.”](#)
- The e300 core PLL (AV_{DD3}) generates the core clock as a slave to the system clock. The frequency ratio between the e300 core clock and the system clock is selected using the e300 PLL ratio configuration bits as described in [Section 22.5, “Core PLL Configuration.”](#)
- The QUICC Engine PLL (AV_{DD1}) which uses the same reference as the system PLL. The QUICC Engine block generates or uses external sources for all required serial interface clocks.

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins. The voltage level at each AV_{DDn} pin should always be equivalent to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in [Figure 44](#), one to each of the five AV_{DD} pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

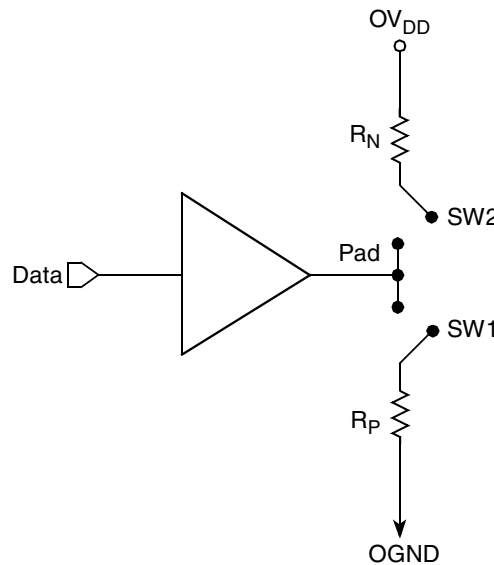


Figure 45. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

[Table 65](#) summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Table 65. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	42 Target	25 Target	20 Target	Z_0	W
R_P	42 Target	25 Target	20 Target	Z_0	W
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See [Table 1](#), $T_j = 105^\circ\text{C}$.

24.6 Configuration Pin Multiplexing

The MPC8323E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

24.7 Pull-Up Resistor Requirements

The MPC8323E requires high resistance pull-up resistors (10 k Ω is recommended) on open drain type pins including I²C pins, Ethernet Management MDIO pin, and IPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see AN3361, “MPC8321E/MPC8323E PowerQUICC Design Checklist,” Rev. 1.

25 Ordering Information

This section presents ordering information for the devices discussed in this document, and it shows an example of how the parts are marked. Ordering information for the devices fully covered by this document is provided in [Section 25.1, “Part Numbers Fully Addressed by This Document.”](#)

25.1 Part Numbers Fully Addressed by This Document

[Table 66](#) provides the Freescale part numbering nomenclature for the MPC8323E family. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the maximum processor core frequency, the part numbering scheme also includes the maximum effective DDR memory speed and QUICC Engine bus frequency. Each part number also contains a revision code which refers to the die mask revision number.

Table 66. Part Numbering Nomenclature

MPC	nnnn	E	C	VR	AF	D	C	A
Product Code	Part Identifier	Encryption Acceleration	Temperature Range ¹	Package ²	e300 Core Frequency ³	DDR Frequency	QUICC Engine Frequency	Revision Level
MPC	8323	Blank = Not included E = included	Blank = 0 to 105°C C = -40 to 105°C	VR = Pb-free PBGA ZQ = Pb PBGA	AD = 266 MHz AF = 333 MHz	D = 266 MHz	C = 200 MHz	Contact local Freescale sales office

Notes:

1. Contact local Freescale office on availability of parts with C temperature range.
2. See [Section 21, “Package and Pin Listings,”](#) for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. Additionally, parts addressed by Part Number Specifications may support other maximum core frequencies.